



A MICROSEMI COMPANY

MWS11-GB11-xx

InGaP HBT Gain Block

PREVIEW

DESCRIPTION

This general purpose amplifier is a low cost, broadband RFIC manufactured with an InGaP/GaAs Heterojunction Bipolar Transistor (HBT) process (MOCVD). This RFIC amplifier was designed as an easily cascadable 50 ohm gain block. The device is self-contained with 50 ohm input and output impedance. Applications include IF and RF amplification in wireless/wired voice and data communication products and broadband test equipment operating up to 6 GHz.

This RFIC amplifier is initially available in a plastic SOT-89 3-Pin package to handle P1dB output power up to 19dBm (5V). The same RFIC will be available later in an advanced Microsemi Gigamite™ package, with significantly smaller footprint for applications where board space is at a premium.

KEY FEATURES

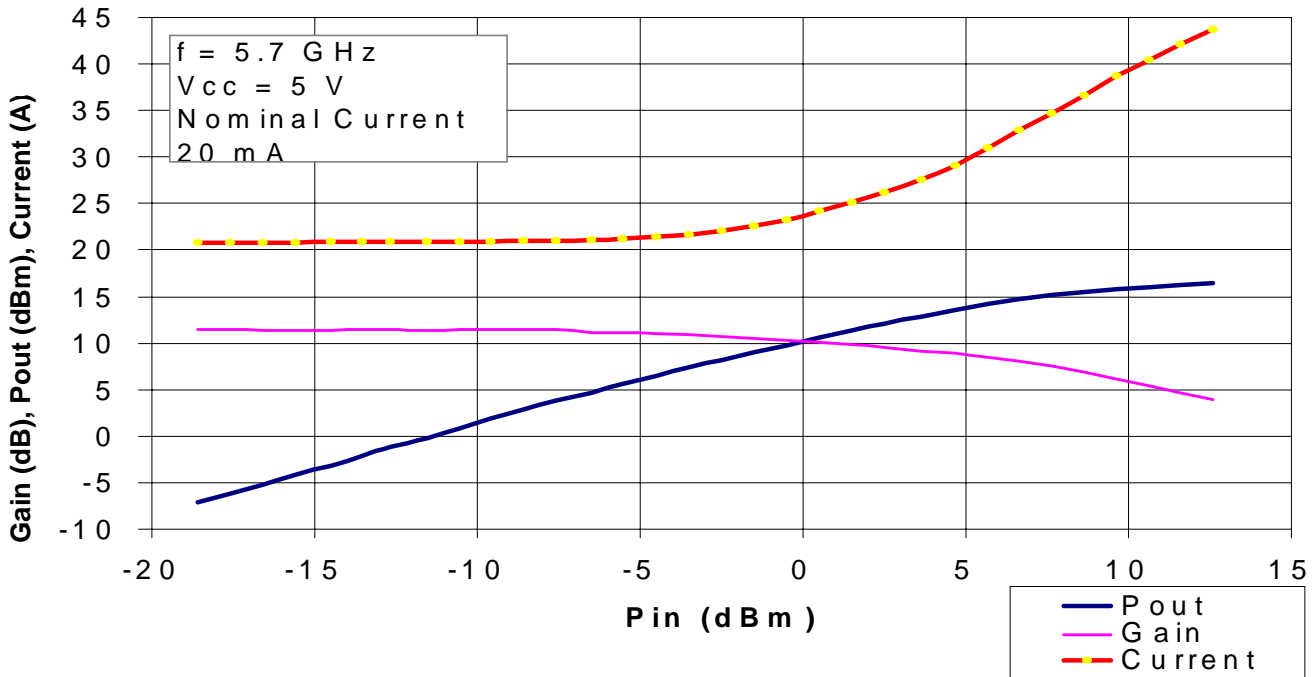
- Advanced InGaP HBT
- DC to 6GHz
- Single +5V Supply
- Small Signal Gain = 16dB
- P1dB = 19dBm (5V), f=1GHz
- SOT-89 3-Pin, & Gigamite Packages

APPLICATIONS/BENEFITS

- Broadband Gain Blocks
- IF or RF buffer Amplifiers
- Driver Stage for Power Amps
- Final Power Amp for Low to Medium Power Applications
- Broadband Test Equipment

IMPORTANT: For the most current data, consult MICROSEMI's website: <http://www.microsemi.com>

PRODUCT HIGHLIGHT



PACKAGE ORDER INFO

PK	Plastic SOT-89 3 Pin	Gigamite
	MWS11GB11-S1	MWS11GB11-G1

Note: Available in Tape & Reel.
Append the letter "T" to the part number. (i.e. MSW11GB11-S89T)